**Product data sheet** 

# 1. General description

Dual common cathode power Schottky diode designed for high frequency switched mode power supplies in a TO220 plastic package.





## 2. Features and benefits

- Trench structure
- High junction temperature up to 150°C
- · Low forward voltage drop, negligible switching losses
- High efficiency

# 3. Applications

- · DC to DC converters
- · Freewheeling diode
- · OR-ing diode
- · Switched mode power supply rectifier

## 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions	Notes	Values		Unit				
Absolute maximum rating										
$V_{RRM}$	repetitive peak reverse voltage				60		V			
I <sub>F(AV)</sub>	average forward current	$δ$ = 0.5 ; square-wave pulse; $T_{mb} \le 129$ °C; per diode; Fig. 1; Fig. 2; Fig. 3		15			A			
I <sub>O(AV)</sub>	average output current	$\delta$ = 0.5 ; square-wave pulse; $T_{mb} \le 130$ °C; both diodes conducting		30			Α			
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit			
Static ch	aracteristics									
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 15 A; T <sub>j</sub> = 25 °C; per diode; <u>Fig. 6</u>		-	0.57	0.65	V			
I <sub>R</sub>	reverse current	$V_R = 60 \text{ V}$ ; $T_j = 25 \text{ °C}$ ; per diode; Fig. 7; Fig. 8		-	40	100	μА			

# 5. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode 1	mb	
2	K	cathode	<del>                                     </del>	A1 A2
3	A2	anode 2		Κ Κ sym125
mb	К	mounting base; connected to cathode		<b>y</b> ,2

# 6. Ordering information

### **Table 3. Ordering information**

Type number	Package name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
WN3S30H60C	TO220	WN3S30H60CQ	Tube	50	SOT78	13-Jun-2008

## 7. Marking

## **Table 4. Marking codes**

Type number	Marking codes
WN3S30H60C	WN3S 30H60C

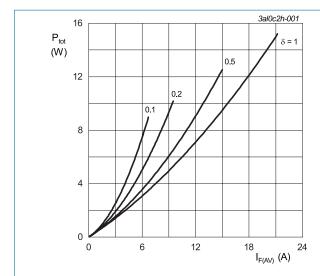
# 8. Limiting values

#### **Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

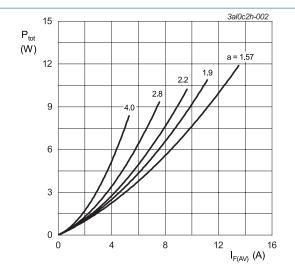
Symbol	Parameter	Conditions	Notes	Values	Unit
$V_{RRM}$	repetitive peak reverse voltage			60	V
$V_{RWM}$	crest working reverse voltage			60	V
$V_R$	reverse voltage	DC		60	V
$I_{F(AV)}$	average forward current	$δ$ = 0.5; square-wave pulse; $T_{mb} \le 129$ °C; per diode; Fig. 1; Fig. 2; Fig. 3		15	А
$I_{O(AV)}$	average output current	$δ$ = 0.5; square-wave pulse; $T_{mb} \le 130$ °C; both diodes conducting		30	Α
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode; Fig. 4		200	А
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode		220	А
T <sub>stg</sub>	storage temperature			-40 to 150	°C
T <sub>j</sub>	junction temperature		[1]	-40 to 150	°C

[1] The heat generated must be less than the thermal conductivity from junction to ambient:  $dP_{tot}/dT_j < 1/R_{th(j-a)}$ 



 $\begin{aligned} & I_{\text{F(AV)}} = I_{\text{F(RMS)}} \times \sqrt{\delta} \\ & V_{\text{o}} = 0.430 \text{ V; } R_{\text{s}} = 0.0135 \text{ } \Omega \end{aligned}$ 

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values; per diode



a = form factor =  $I_{F(RMS)}$  /  $I_{F(AV)}$ V<sub>o</sub> = 0.430 V; R<sub>s</sub> = 0.0135  $\Omega$ 

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values; per diode

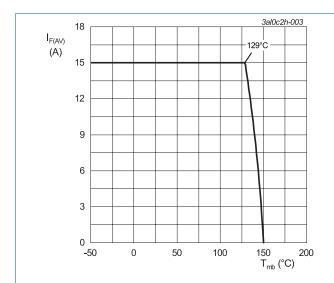


Fig. 3. Average forward current as a function of mounting base temperature; maximum values; per diode

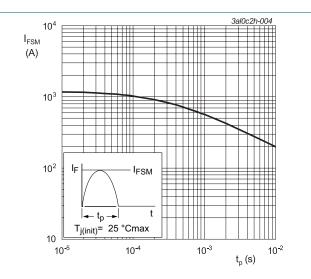


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values; per diode

## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
$R_{\text{th(j-mb)}}$	thermal resistance from junction to	per diode; Fig. 5		-	-	1.7	K/W
	mounting base	both diodes conducting		-	-	8.0	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air		-	60	-	K/W

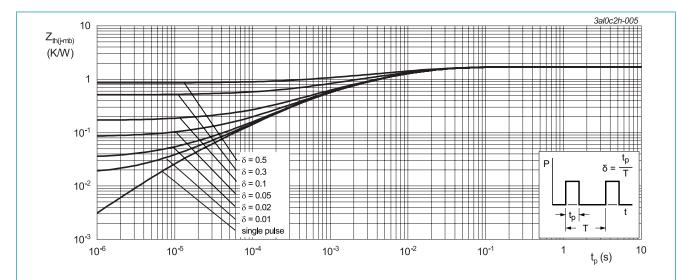
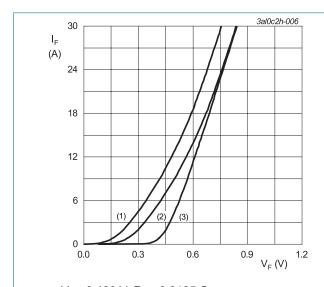


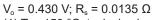
Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration; maximum values; per diode

## 10. Characteristics

**Table 7. Characteristics** 

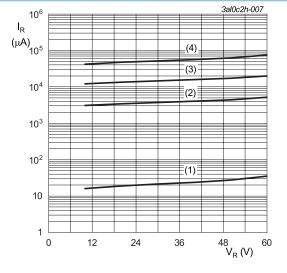
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
Static cha	aracteristics						
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 15 A; T <sub>j</sub> = 25 °C; per diode; <u>Fig. 6</u>		-	0.57	0.65	V
		I <sub>F</sub> = 15 A; T <sub>j</sub> = 125 °C; per diode; <u>Fig. 6</u>		-	0.55	-	V
		I <sub>F</sub> = 3 A; T <sub>j</sub> = 25 °C; per diode; <u>Fig. 6</u>		-	0.39	-	V
		I <sub>F</sub> = 3 A; T <sub>j</sub> = 125 °C; per diode; <u>Fig. 6</u>		-	0.29	-	V
I <sub>R</sub>	reverse current	$V_R = 60 \text{ V; } T_j = 25 \text{ °C; per diode;}$ Fig. 7; Fig. 8		-	40	100	μΑ
		V <sub>R</sub> = 60 V; T <sub>j</sub> = 125 °C; per diode; Fig. 7; Fig. 8		-	25	100	mA





<sup>(1)</sup>  $T_j$  = 150 °C; typical values

Fig. 6. Forward current as a function of forward voltage; per diode



(1) T<sub>i</sub> = 25 °C; typical values

(3) 
$$T_j = 125 \,^{\circ}\text{C}$$
; typical values

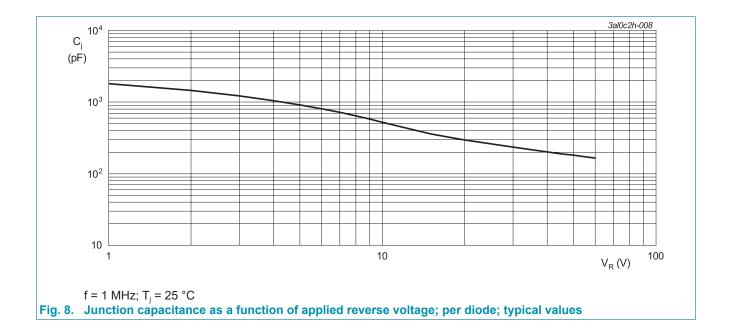
Fig. 7. Reverse leakage current as a function of reverse voltage; per diode; typical values

<sup>(2)</sup> T<sub>i</sub> = 150 °C; maximum values

<sup>(3)</sup> T<sub>i</sub> = 25 °C; maximum values

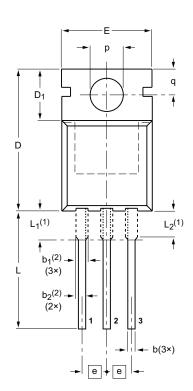
<sup>(2)</sup> T<sub>j</sub> = 100 °C; typical values

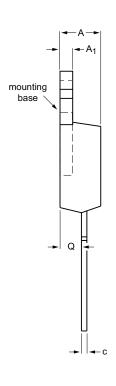
<sup>(4)</sup> T<sub>i</sub> = 150 °C; typical values



# 11. Package outline







0 5 10 mm scale

### **DIMENSIONS** (mm are the original dimensions)

UNIT	A	A <sub>1</sub>	b	b <sub>1</sub> <sup>(2)</sup>	b <sub>2</sub> <sup>(2)</sup>	С	D	D <sub>1</sub>	E	е	L	L <sub>1</sub> <sup>(1)</sup>	L <sub>2</sub> <sup>(1)</sup> max.	р	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

#### Notes

- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTLINE		REFERENCES		EUROPEAN	ISSUE DATE	
VERSION	IEC	IEC JEDEC JEITA	JEITA	PROJECTION	1330E DATE	
SOT78		3-lead TO-220AB	SC-46	$ \  \                                $	<del>08-04-23</del> 08-06-13	

## 12. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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WN3S30H60C

**Dual power Schottky diode** 

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